

## Cool MOS™ Power Transistor

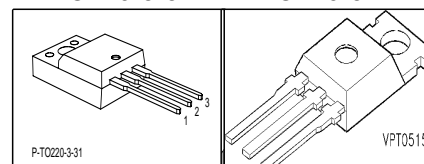
### Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- Ultra low effective capacitances
- Improved transconductance
- P-TO-220-3-31: Fully isolated package (2500 VAC; 1 minute)

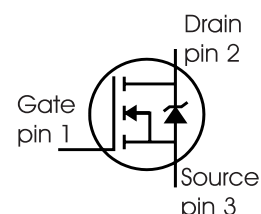
$V_{DS}$	800	V
$R_{DS(on)}$	0.45	$\Omega$
$I_D$	11	A

P-TO220-3-31

P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP11N80C3	P-TO220-3-1	Q67040-S4438	11N80C3
SPA11N80C3	P-TO220-3-31	Q67040-S4439	11N80C3



### Maximum Ratings

Parameter	Symbol	Value		Unit
		SPP	SPA	
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	$I_D$	11 7.1	11 <sup>1)</sup> 7.1 <sup>1)</sup>	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_D$ puls	33	33	A
Avalanche energy, single pulse $I_D=2.2\text{A}$ , $V_{DD}=50\text{V}$	$E_{AS}$	470	470	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>2)</sup> $I_D=11\text{A}$ , $V_{DD}=50\text{V}$	$E_{AR}$	0.2	0.2	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	11	11	A
Gate source voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{Hz}$ )	$V_{GS}$	$\pm 30$	$\pm 30$	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	156	41	W
Operating and storage temperature	$T_j$ , $T_{stg}$	-55...+150		$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 640 \text{ V}, I_D = 11 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.8	K/W
Thermal resistance, junction - case, FullPAK	$R_{thJC \text{ FP}}$	-	-	3.7	
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
Thermal resistance, junction - ambient, FullPAK	$R_{thJA \text{ FP}}$	-	-	80	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s <sup>3</sup> )	$T_{sold}$	-	-	260	$^\circ\text{C}$

**Electrical Characteristics, at  $T_j=25^\circ\text{C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=0.25\text{mA}$	800	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}, I_D=11\text{A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=680\mu\text{A}, V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.5	20	$\mu\text{A}$
			-	-	200	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=7.1\text{A}$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.39	0.45	$\Omega$
			-	1.1	-	
Gate input resistance	$R_G$	$f=1\text{MHz}, \text{open drain}$	-	0.7	-	

**Electrical Characteristics**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 7.1A$	-	7.5	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1MHz$	-	1600	-	pF
Output capacitance	$C_{oss}$		-	800	-	
Reverse transfer capacitance	$C_{rss}$		-	40	-	
Effective output capacitance, <sup>4)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0V$ , $V_{DS} = 0V$ to 480V	-	44.3	-	
Effective output capacitance, <sup>5)</sup> time related	$C_{o(tr)}$		-	33.9	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400V$ , $V_{GS} = 0/10V$ , $I_D = 11A$ , $R_G = 7.5\Omega$	-	25	-	ns
Rise time	$t_r$		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	82	
Fall time	$t_f$		-	7	10	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 640V$ , $I_D = 11A$	-	6	-	nC
Gate to drain charge	$Q_{gd}$		-	25	-	
Gate charge total	$Q_g$	$V_{DD} = 640V$ , $I_D = 11A$ , $V_{GS} = 0$ to 10V	-	50	60	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640V$ , $I_D = 11A$	-	6	-	V

<sup>1</sup>Limited only by maximum temperature

<sup>2</sup>Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>3</sup>Soldering temperature for TO-263: 220°C, reflow

<sup>4</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

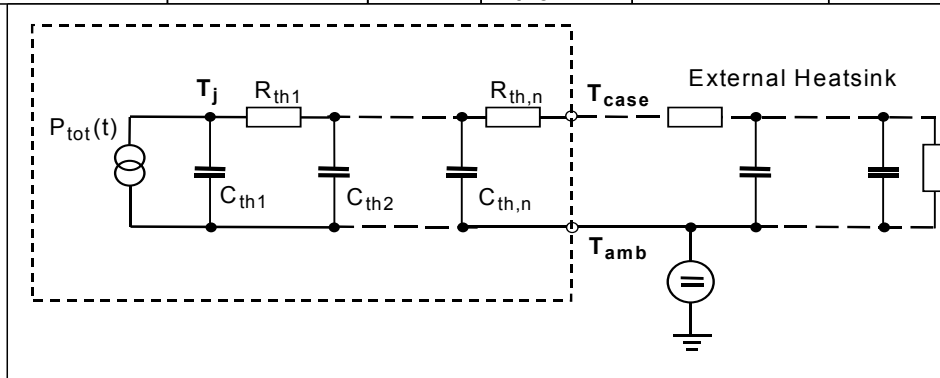
<sup>5</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	11	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	33	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=640\text{V}, I_F=I_S,$	-	550	-	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	10	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	33	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$	$T_j=25^\circ\text{C}$	-	1000	-	$\text{A}/\mu\text{s}$

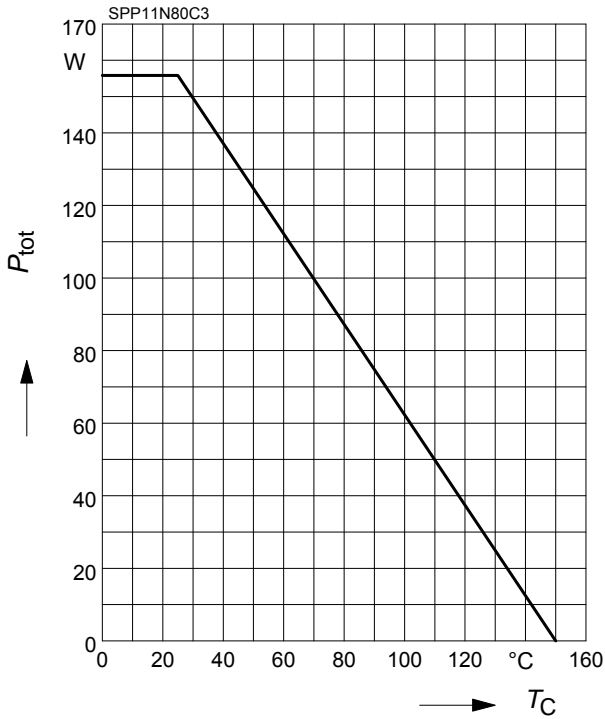
**Typical Transient Thermal Characteristics**

Symbol	Value		Unit	Symbol	Value		Unit
	SPP	SPA			SPP	SPA	
$R_{th1}$	0.012	0.012	K/W	$C_{th1}$	0.0002493	0.0002493	Ws/K
$R_{th2}$	0.023	0.023		$C_{th2}$	0.0009399	0.0009399	
$R_{th3}$	0.043	0.043		$C_{th3}$	0.001298	0.001298	
$R_{th4}$	0.154	0.176		$C_{th4}$	0.003617	0.003617	
$R_{th5}$	0.175	0.371		$C_{th5}$	0.009186	0.00802	
$R_{th6}$	0.071	2.522		$C_{th6}$	0.074	0.412	



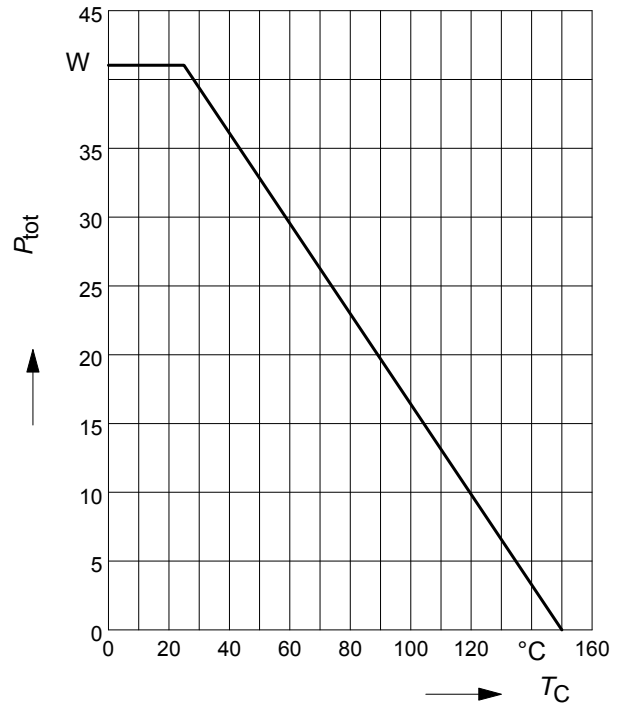
**1 Power dissipation**

$$P_{tot} = f(T_C)$$



**2 Power dissipation FullPAK**

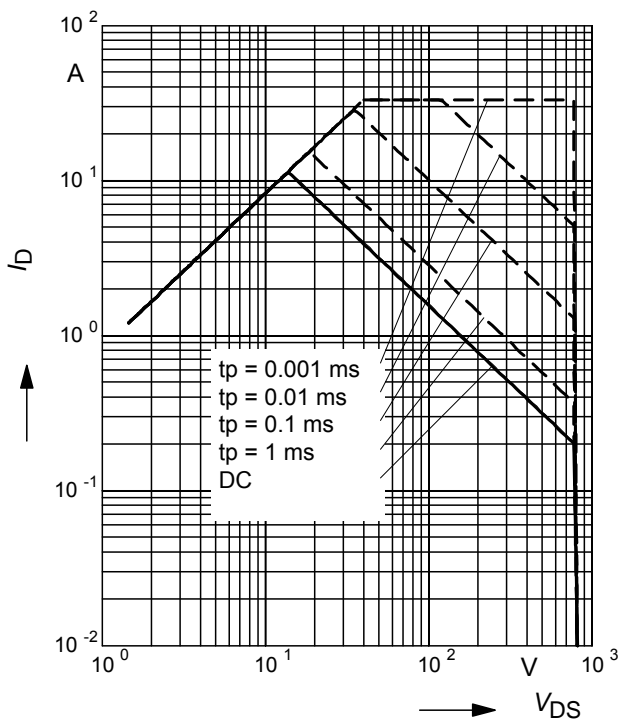
$$P_{tot} = f(T_C)$$



**3 Safe operating area**

$$I_D = f(V_{DS})$$

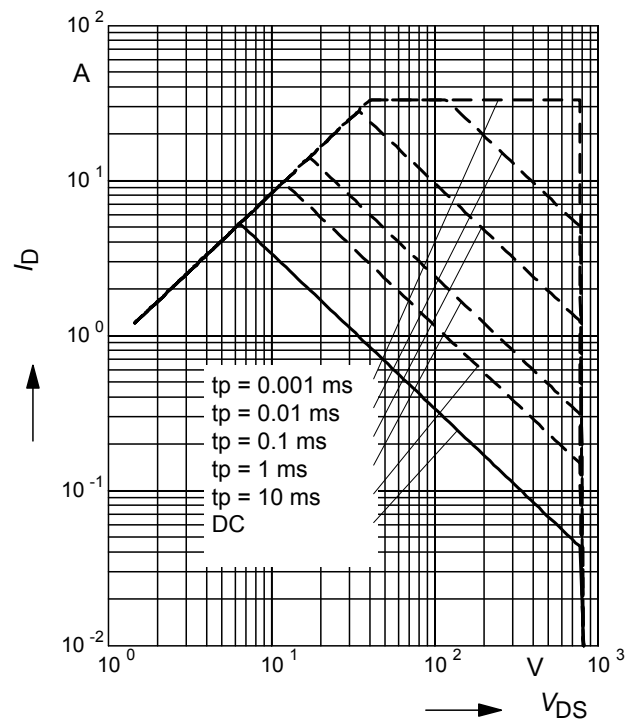
parameter :  $D = 0$  ,  $T_C = 25^\circ\text{C}$



**4 Safe operating area FullPAK**

$$I_D = f(V_{DS})$$

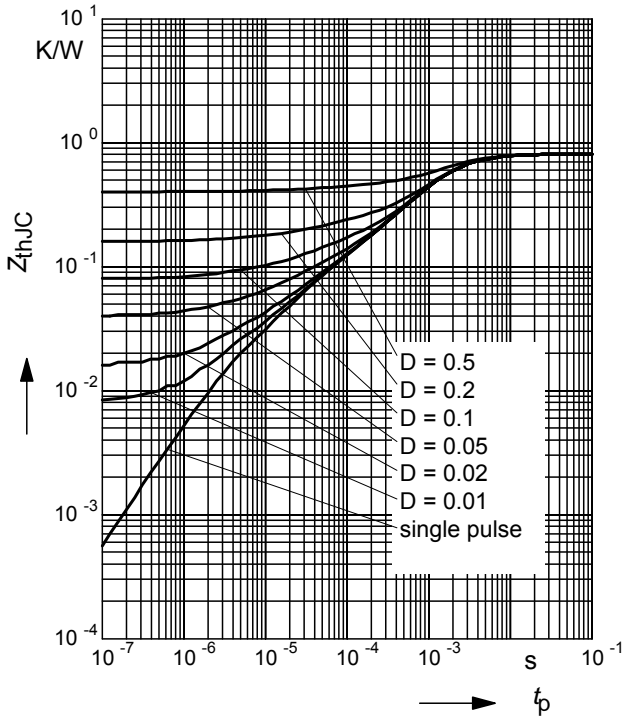
parameter:  $D = 0$  ,  $T_C = 25^\circ\text{C}$



**5 Transient thermal impedance**

$Z_{thJC} = f(t_p)$

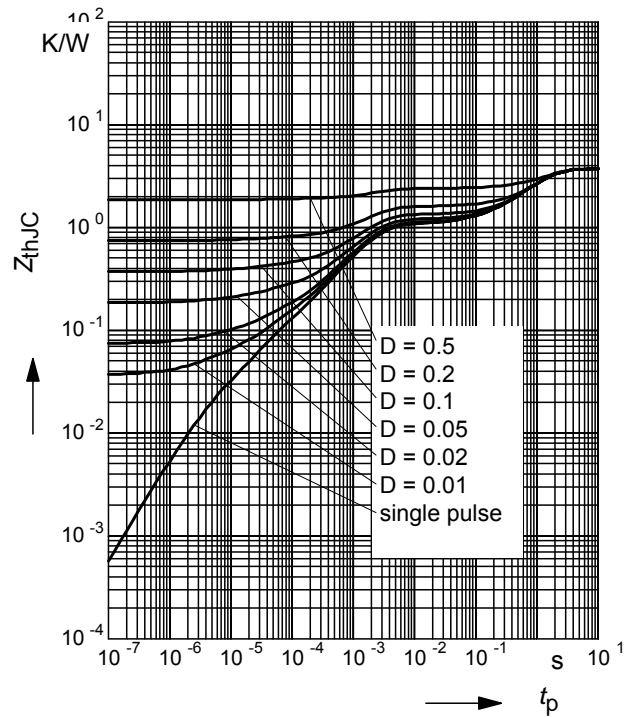
parameter:  $D = t_p/T$



**6 Transient thermal impedance FullPAK**

$Z_{thJC} = f(t_p)$

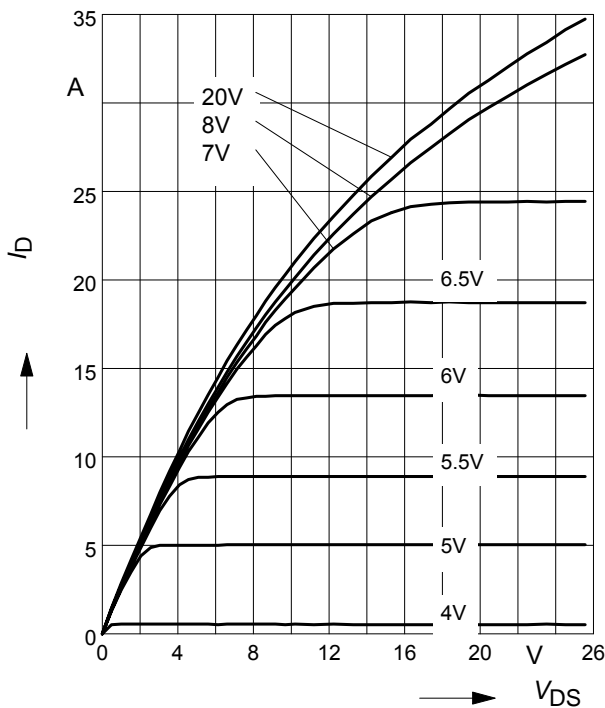
parameter:  $D = t_p/t$



**7 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ C$

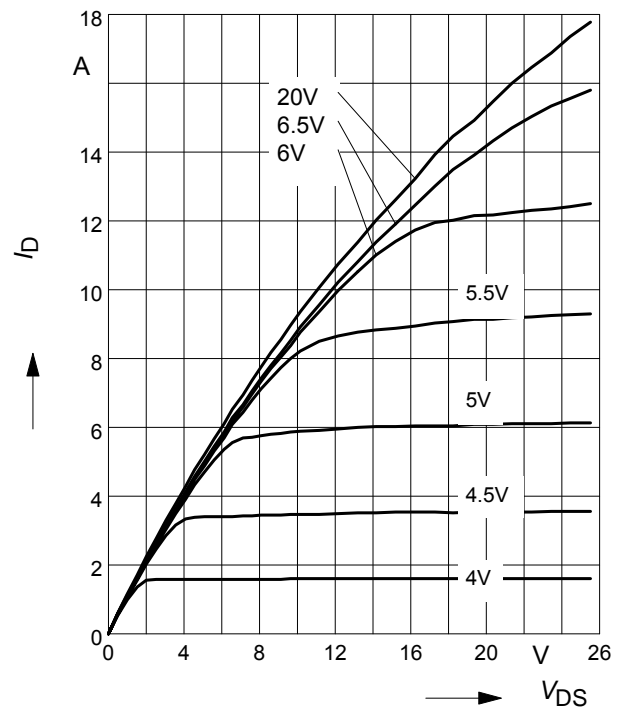
parameter:  $t_p = 10 \mu s, V_{GS}$



**8 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ C$

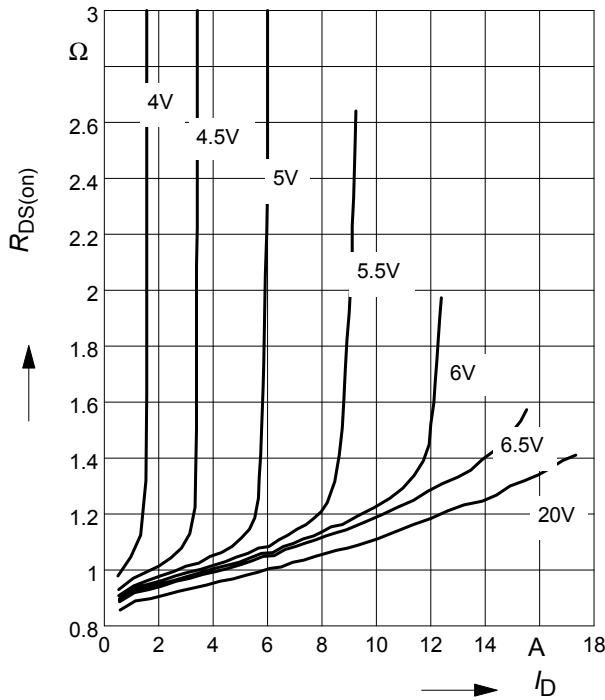
parameter:  $t_p = 10 \mu s, V_{GS}$



**9 Typ. drain-source on resistance**

$$R_{DS(on)} = f(I_D)$$

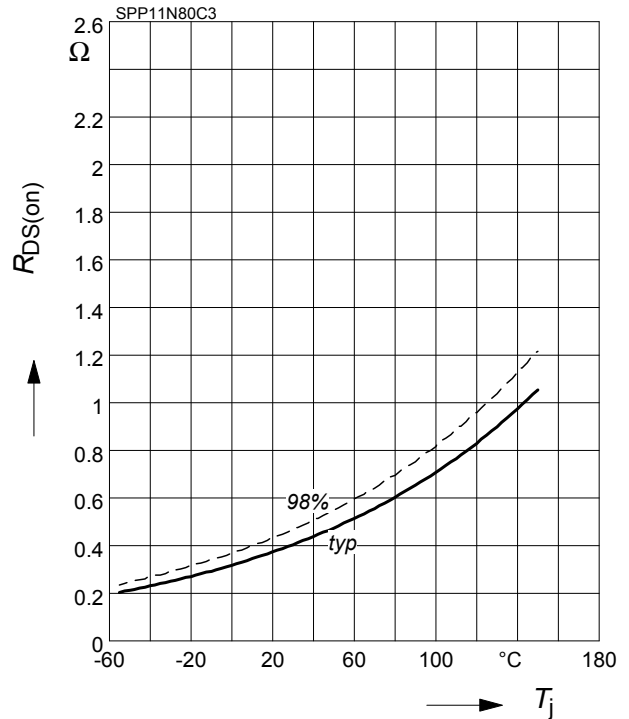
parameter:  $T_j = 150^\circ\text{C}$ ,  $V_{GS}$



**10 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

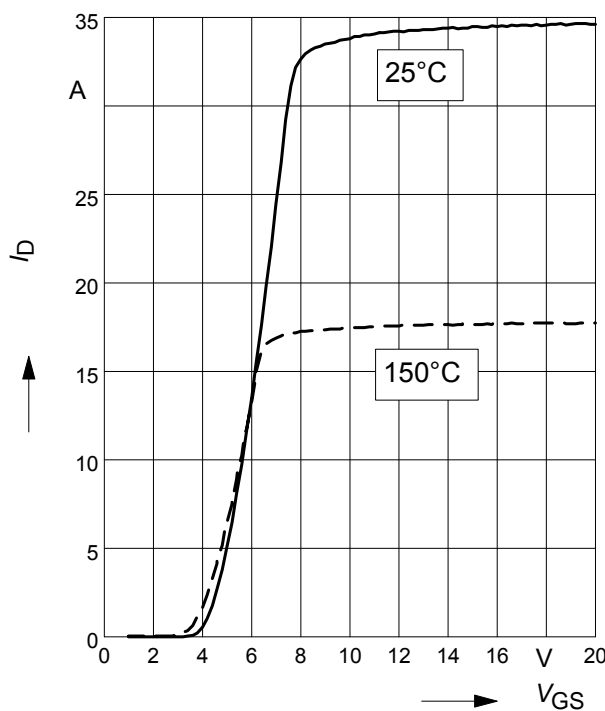
parameter:  $I_D = 7.1\text{ A}$ ,  $V_{GS} = 10\text{ V}$



**11 Typ. transfer characteristics**

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

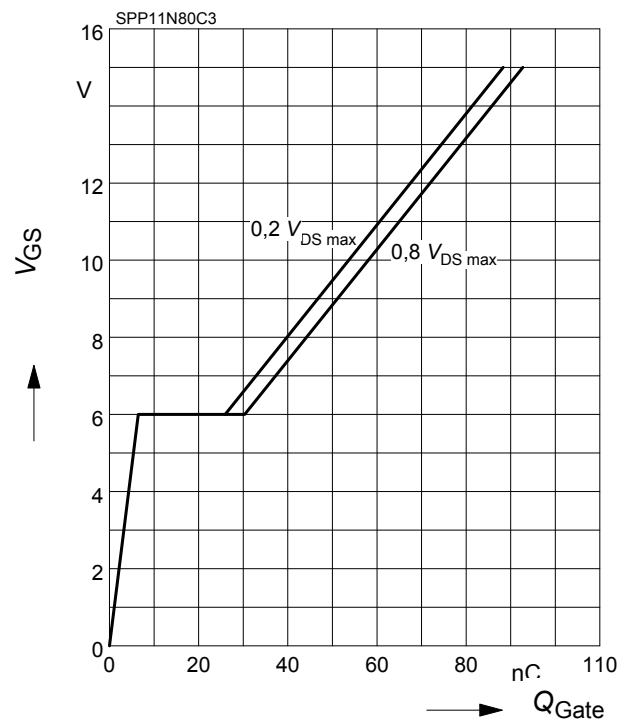
parameter:  $t_p = 10\ \mu\text{s}$



**12 Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

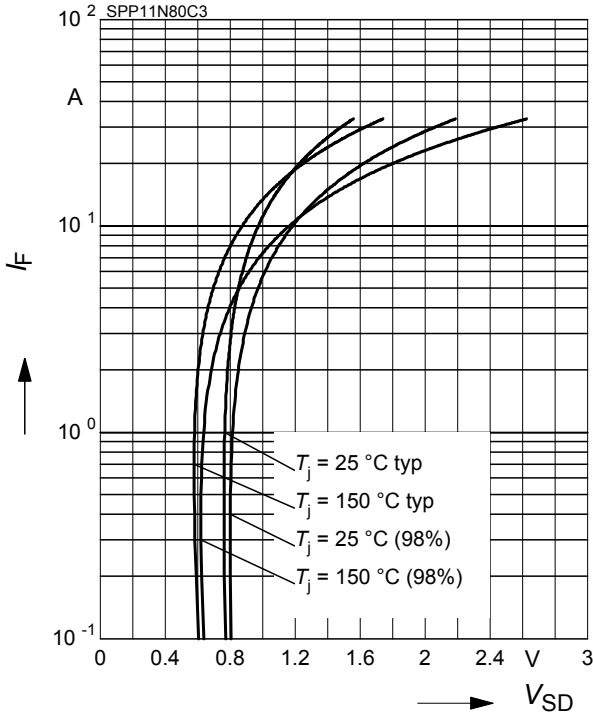
parameter:  $I_D = 11\text{ A pulsed}$



**13 Forward characteristics of body diode**

$$I_F = f(V_{SD})$$

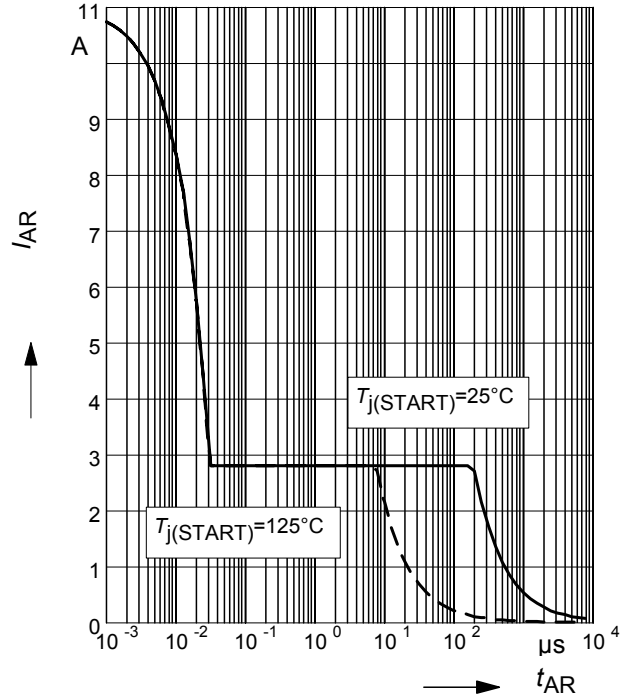
parameter:  $T_j$ ,  $t_p = 10 \mu s$



**14 Avalanche SOA**

$$I_{AR} = f(t_{AR})$$

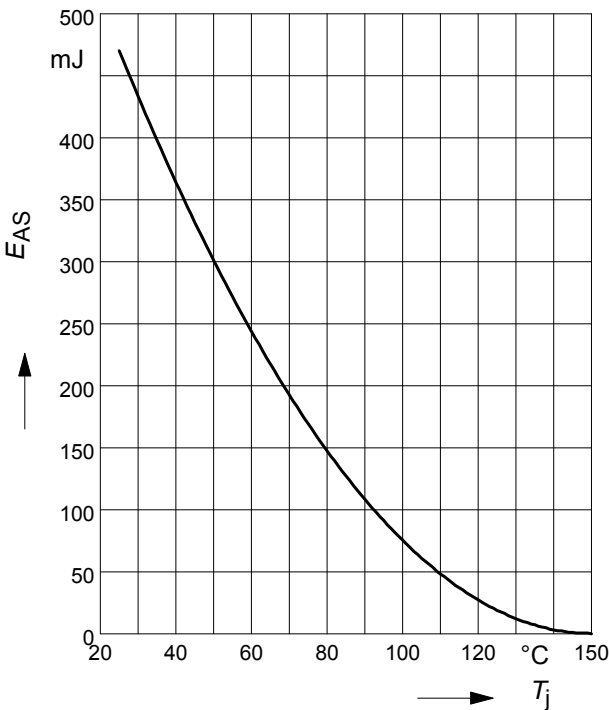
par.:  $T_j \leq 150 \text{ °C}$



**15 Avalanche energy**

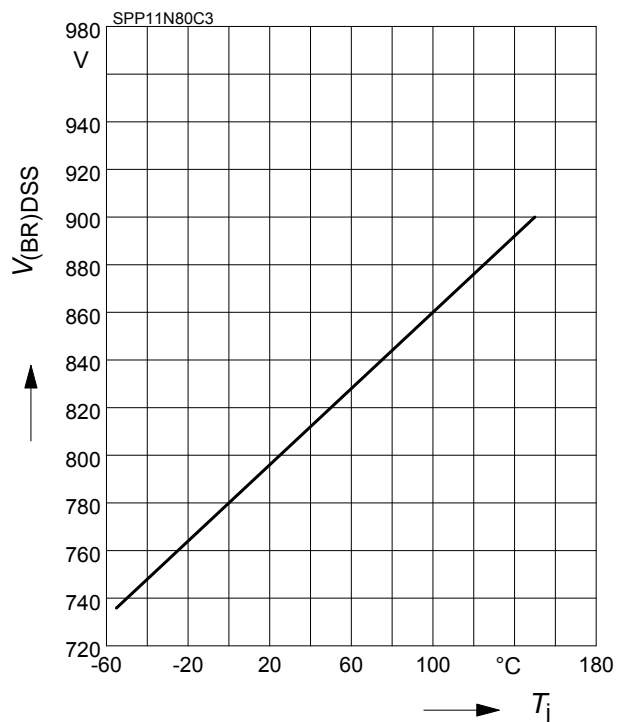
$$E_{AS} = f(T_j)$$

par.:  $I_D = 2.2 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$



**16 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$

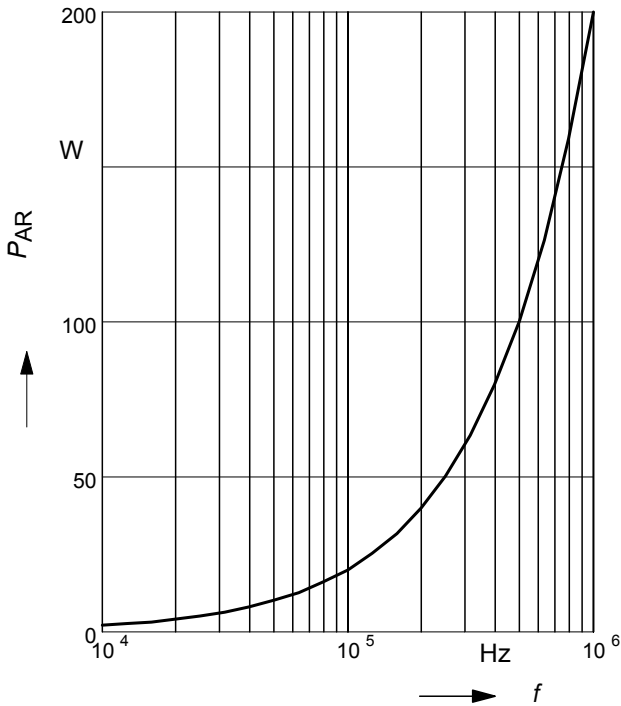




**17 Avalanche power losses**

$$P_{AR} = f(f)$$

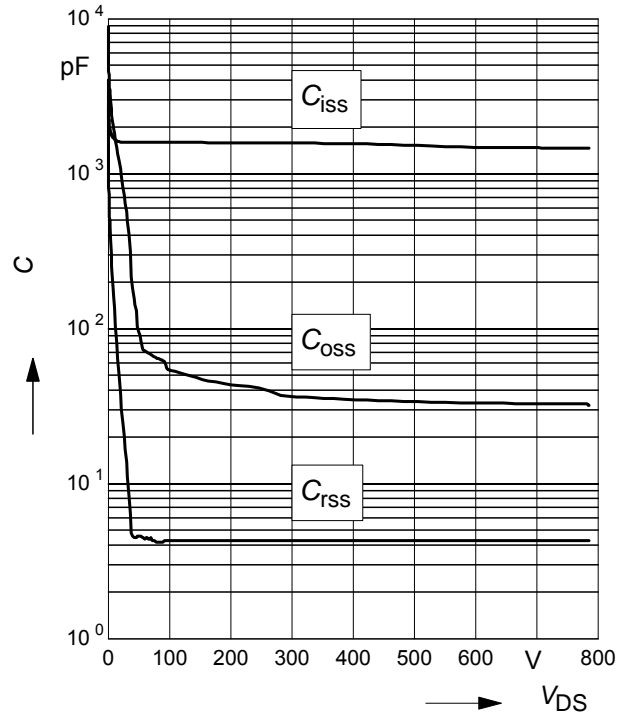
parameter:  $E_{AR}=0.2\text{mJ}$



**18 Typ. capacitances**

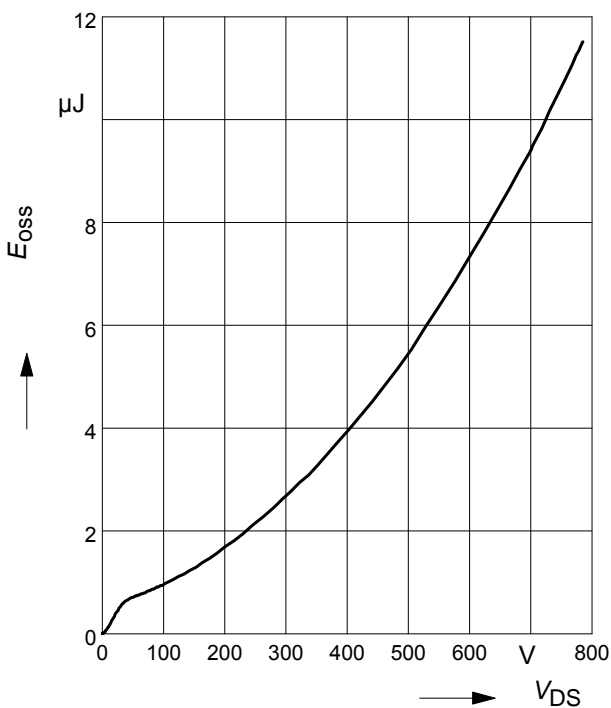
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0\text{V}$ ,  $f=1\text{ MHz}$

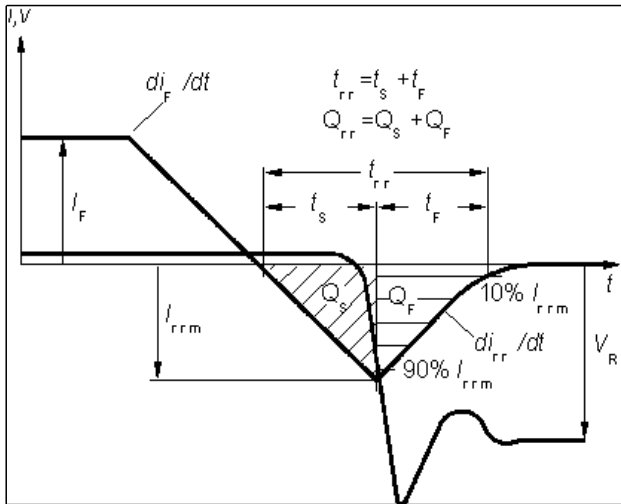


**19 Typ.  $C_{oss}$  stored energy**

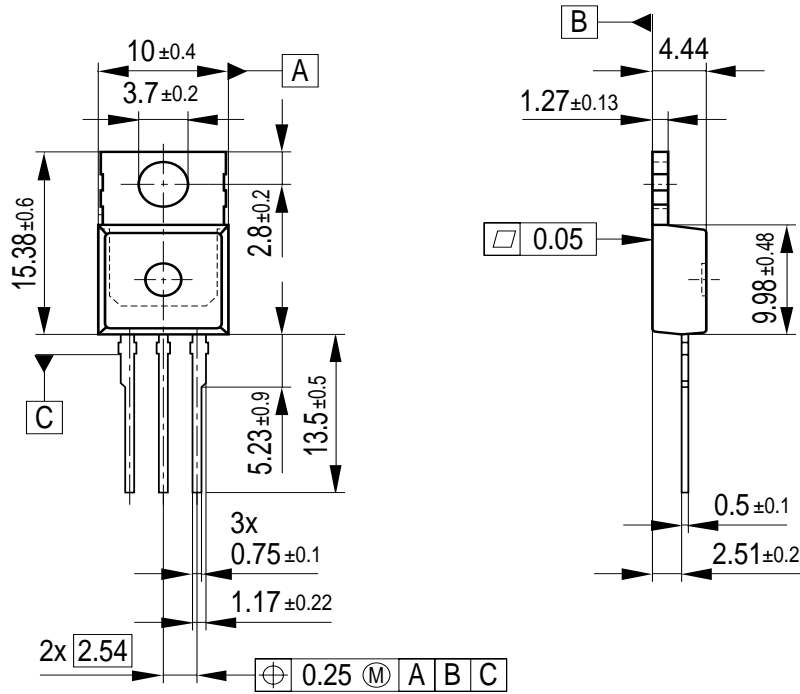
$$E_{oss} = f(V_{DS})$$



Definition of diodes switching characteristics

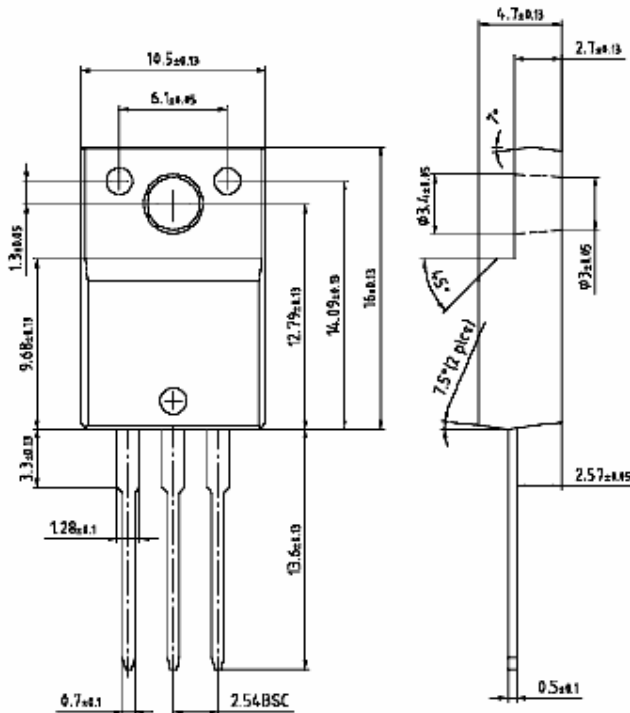


P-TO-220-3-1



All metal surfaces tin plated, except area of cut.  
Metal surface min.  $x=7.25$ ,  $y=12.3$

P-TO-220-3-31 (FullPAK)



Please refer to mounting instructions (application note AN-TO220-3-31-01)

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